OP \$40.00 2896625

ETAS ID: TM321200

TRADEMARK ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

SUBMISSION TYPE: NEW ASSIGNMENT

NATURE OF CONVEYANCE: Security Agreement

CONVEYING PARTY DATA

| Name | Formerly | Execution Date | Entity Type |
|-----------------|----------|----------------|-----------------------|
| Anadigics, Inc. | | 10/24/2014 | CORPORATION: DELAWARE |

RECEIVING PARTY DATA

| Name: | Silicon Valley Bank |
|-------------------|-------------------------|
| Street Address: | 275 Grove Street |
| Internal Address: | Suite 2-200 |
| City: | Newton |
| State/Country: | MASSACHUSETTS |
| Postal Code: | 02466 |
| Entity Type: | CORPORATION: CALIFORNIA |

PROPERTY NUMBERS Total: 1

| Property Type | Number | Word Mark |
|----------------------|---------|-----------|
| Registration Number: | 2896625 | ANADIGICS |

CORRESPONDENCE DATA

Fax Number: 8004947512

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent

using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 202-370-4750

Email: ipteam@nationalcorp.com

Correspondent Name: Dwayne C. Houston

Address Line 1: 1025 Vermont Avenue NW, Suite 1130

Address Line 2: National Corporate Research, Ltd.

Address Line 4: Washington, D.C. 20005

| ATTORNEY DOCKET NUMBER: | F152345 |
|-------------------------|---------------------|
| NAME OF SUBMITTER: | Matthew R. Pierce |
| SIGNATURE: | /Matthew R. Pierce/ |
| DATE SIGNED: | 10/27/2014 |

Total Attachments: 16

source=Intellectual Property Security Agreement - Anadigics, Inc. - Trademark Filing#page2.tif source=Intellectual Property Security Agreement - Anadigics, Inc. - Trademark Filing#page3.tif source=Intellectual Property Security Agreement - Anadigics, Inc. - Trademark Filing#page4.tif source=Intellectual Property Security Agreement - Anadigics, Inc. - Trademark Filing#page5.tif

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INTELLECTUAL PROPERTY SECURITY AGREEMENT

This Intellectual Property Security Agreement (this "Agreement") is entered into as of October 24, 2014 by and between **SILICON VALLEY BANK**, a California corporation, with a loan production office located at 275 Grove Street, Suite 2-200, Newton, Massachusetts 02466 ("Bank") and **ANADIGICS**, INC., a Delaware corporation, with its principal place of business located at 141 Mount Bethel Road, Warren, New Jersey 07059 ("Grantor").

RECITALS

- A. Bank has agreed to make certain advances of money and to extend certain financial accommodations to Grantor (the "Loans"), in the amounts and manner set forth in that certain Loan and Security Agreement by and between Bank and Grantor dated as of even date herewith (as the same may be amended, modified, restated and/or supplemented from time to time, the "Loan Agreement"; capitalized terms used herein are used as defined in the Loan Agreement). Bank is willing to make the Loans to Grantor, but only upon the condition, among others, that Grantor shall grant to Bank a security interest in its Copyrights, Trademarks, Patents, and Mask Works (as each term is described below) to secure the obligations of Grantor to Bank.
- B. Pursuant to the terms of the Loan Agreement, Grantor has granted to Bank a security interest in all of Grantor's right, title and interest, whether presently existing or hereafter acquired, in, to and under all of the Collateral.

NOW, THEREFORE, for good and valuable consideration, receipt of which is hereby acknowledged, and intending to be legally bound, as collateral security for the prompt and complete payment when due of Grantor's obligations to Bank, Grantor hereby represents, warrants, covenants and agrees as follows:

AGREEMENT

- 1. <u>Grant of Security Interest.</u> To secure Grantor's obligations to Bank, Grantor grants and pledges to Bank a security interest in all of Grantor's right, title and interest in, to and under its intellectual property (all of which shall collectively be called the "Intellectual Property Collateral"), including, without limitation, the following:
- (a) Any and all copyright rights, copyright applications, copyright registrations and like protections in each work of authorship and derivative work thereof, whether published or unpublished and whether or not the same also constitutes a trade secret, now or hereafter existing, created, acquired or held, including without limitation those set forth on Exhibit A attached hereto (collectively, the "Copyrights");
- (b) Any and all trade secrets, and any and all intellectual property rights in computer software and computer software products now or hereafter existing, created, acquired or held;
- (c) Any and all design rights that may be available to Grantor now or hereafter existing, created, acquired or held;
- (d) All patents, patent applications and like protections including, without limitation, improvements, divisions, continuations, renewals, reissues, extensions and continuations-in-part of the

same, including without limitation the patents and patent applications set forth on Exhibit B attached hereto (collectively, the "Patents");

- (e) Any trademark and servicemark rights, whether registered or not, applications to register and registrations of the same and like protections, and the entire goodwill of the business of Grantor connected with and symbolized by such trademarks, including without limitation those set forth on Exhibit C attached hereto (collectively, the "Trademarks");
- (f) All mask works or similar rights available for the protection of semiconductor chips, now owned or hereafter acquired, including, without limitation those set forth on Exhibit D attached hereto (collectively, the "Mask Works");
- (g) Any and all claims for damages by way of past, present and future infringements of any of the rights included above, with the right, but not the obligation, to sue for and collect such damages for said use or infringement of the intellectual property rights identified above;
- (h) All licenses or other rights to use any of the Copyrights, Patents, Trademarks, or Mask Works and all license fees and royalties arising from such use to the extent permitted by such license or rights;
- (i) All amendments, extensions, renewals and extensions of any of the Copyrights, Trademarks, Patents, or Mask Works; and
- (j) All proceeds and products of the foregoing, including without limitation all payments under insurance or any indemnity or warranty payable in respect of any of the foregoing.
- 2. <u>Recordation.</u> Grantor authorizes the Commissioner for Patents, the Commissioner for Trademarks and the Register of Copyrights and any other government officials to record and register this Agreement upon request by Bank.
- 3. <u>Loan Documents</u>. This Agreement has been entered into pursuant to and in conjunction with the Loan Agreement, which is hereby incorporated by reference. The provisions of the Loan Agreement shall supersede and control over any conflicting or inconsistent provision herein. The rights and remedies of Bank with respect to the Intellectual Property Collateral are as provided by the Loan Agreement and related documents, and nothing in this Agreement shall be deemed to limit such rights and remedies.
- 4. <u>Execution in Counterparts</u>. This Agreement may be executed in counterparts (and by different parties hereto in different counterparts), each of which shall constitute an original, but all of which when taken together shall constitute a single contract. Delivery of an executed counterpart of a signature page to this Agreement by facsimile or in electronic (i.e., "pdf" or "tif" format) shall be effective as delivery of a manually executed counterpart of this Agreement.
- 5. <u>Successors and Assigns</u>. This Agreement will be binding on and shall inure to the benefit of the parties hereto and their respective successors and assigns.
- 6. Governing Law. This Agreement and any claim, controversy, dispute or cause of action (whether in contract or tort or otherwise) based upon, arising out of or relating to this Agreement and the transactions contemplated hereby and thereby shall be governed by, and construed in accordance with, the laws of the United States and the State of New York, without giving effect to any choice or conflict of law provision or rule (whether of the State of New York or any other jurisdiction).

[Signature page follows.]

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

| GRANTOR: |
|---------------------|
| ANADIGICS, INC. |
| By: In 1 100/ |
| Title: VP-CFO |
| |
| |
| BANK: |
| SILICON VALLEY BANK |
| Ву: |
| Title: |

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

| GRANTOR: |
|----------------------|
| ANADIGICS, INC. |
| Ву: |
| Title: |
| |
| |
| BANK: |
| SILICON VALLEY BANK |
| By: Michael ann |
| Title: \mathcal{P} |

EXHIBIT A

Please refer to Exhibit D

EXHIBIT B

Patents

| U.S. ISSUED PATENTS | | |
|---|-----------|------------|
| TITLE | PAT. NO. | ISSUE DATE |
| Protection circuit for an electronic circuit | 8,767,361 | 7/1/2014 |
| Protection circuit | 8,743,518 | 6/3/2014 |
| RF directional coupled output from a quadrature combined amplifier | 8,737,520 | 5/27/2014 |
| Reconfigureable output matching network for multi band RF power amplifier | 8,736,378 | 5/27/2014 |
| Multistage amplification and high dynamic range rectification circuit | 8,724,355 | 5/13/2014 |
| Vector voltage samplers for RF interface control of power amplifier | 8,717,104 | 5/6/2014 |
| Current mirror circuit | 8,717,092 | 5/6/2014 |
| Low leakage logic circuit | 8,680,885 | 3/25/2014 |
| Current limiting circuit | 8,648,661 | 2/11/2014 |
| Linear multi-mode power amplifier for dynamic supply operation | 8,598,951 | 12/3/2013 |
| Tunable directional power combiner | 8,508,296 | 8/13/2013 |
| Direct DC coupled push-pull BJT driver for power amplifier with built- in gain and bias current signal dependent expansion | 8,497,736 | 7/30/2013 |
| Wideband RF power amplifier for multi-mode multi-band applications | 8,461,931 | 6/11/2013 |
| Power control circuit for radio frequency power amplifiers | 8,432,228 | 4/30/2013 |
| Power amplifier protection circuit | 8,258,876 | 9/4/2012 |
| Multi-stage power amplifier with enhanced efficiency | 8,130,043 | 3/6/2012 |
| Timing functions to optimize code-execution time | 7,890,288 | 2/15/2011 |
| Temperature compensated power detector | 7,890,065 | 2/15/2011 |
| High-power switch | 7,852,172 | 12/14/2010 |
| System and method for frequency multiplexing in double-conversion receivers | 7,830,456 | 11/9/2010 |
| Tuning circuitry utilizing frequency translation of an impedance from a fixed-filter frequency response | 7,764,942 | 7/27/2010 |

| Structures and methods for fabricating vertically integrated HBT-FET device | 7,718,486 | 5/18/2010 |
|--|-----------|------------|
| Tunable balanced loss compensation in an electronic filter | 7,639,069 | 12/29/2009 |
| Electrostatic discharge protection device | 7,586,720 | 9/8/2009 |
| Voltage regulated power supply system | 7,564,230 | 7/21/2009 |
| Device and method for power amplifier noise reduction | 7,545,218 | 6/9/2009 |
| System and method for improving power efficiency in GSM power amplifiers | 7,545,217 | 6/9/2009 |
| System and method for distortion cancellation in amplifiers | 7,459,974 | 12/2/2008 |
| CDMA power amplifier design for low and high power modes | 7,443,236 | 10/28/2008 |
| Method and system for image rejection by using post mixer I/Q equalization | 7,400,873 | 7/15/2008 |
| Power amplifier having curve-fitting predistorter | 7,385,447 | 6/10/2008 |
| Device and method for power amplifier noise reduction | 7,348,852 | 3/25/2008 |
| System and method for distortion cancellation in amplifiers | 7,301,396 | 11/27/2007 |
| Variable gain amplifier | 7,292,104 | 11/6/2007 |
| Multi-mode digital bias control for enhancing power amplifier efficiency | 7,248,111 | 7/24/2007 |
| CDMA power amplifier design for low and high power modes | 7,202,736 | 4/10/2007 |
| Method and apparatus for gain control | 7,173,406 | 2/6/2007 |
| Method and apparatus for compensating and improving efficiency in a variable power amplifier | 7,102,444 | 9/5/2006 |
| Electrostatic discharge protection device | 7,071,514 | 7/4/2006 |
| Temperature compensated bias network | 7,019,508 | 3/28/2006 |
| Structures and methods for fabricating vertically integrated HBT/FET device | 7,015,519 | 3/21/2006 |
| Method and apparatus for optimization of amplifier with adjustable output range | 7,009,454 | 3/7/2006 |
| Monolithically fabricated HBT amplification stage with current limiting FET | 6,998,920 | 2/14/2006 |
| Efficiency enhancement for MMIC amplifiers | 6,970,039 | 11/29/2005 |
| Low bias current/temperature compensation current mirror for linear power amplifier | 6,937,102 | 8/30/2005 |

| Bias circuit linearization and dynamic power control | 6,882,227 | 4/19/2005 |
|--|-----------|------------|
| Compact layout for a semiconductor device | 6,856,004 | 2/15/2005 |
| Transient overvoltage protection circuit | 6,853,526 | 2/8/2005 |
| Gain block with stable internal bias from low-voltage power supply | 6,842,075 | 1/11/2005 |
| Power amplifier with load switching circuit | 6,806,767 | 10/19/2004 |
| Dynamic matching in cascode circuits | 6,803,824 | 10/12/2004 |
| Integrated circuits with scalable design | 6,760,900 | 7/6/2004 |
| High directivity multi-band coupled-line coupler for RF power amplifier | 6,759,922 | 7/6/2004 |
| Multi-mode amplifier bias circuit | 6,753,734 | 6/22/2004 |
| Low stress thermal and electrical interconnects for heterojunction bipolar transistors | 6,724,067 | 4/20/2004 |
| Portable tube holder apparatus | 6,719,518 | 4/13/2004 |
| Gain control circuit with well-defined gain states | 6,710,657 | 3/23/2004 |
| Laser-trimmable digital resistor | 6,664,500 | 12/16/2003 |
| System and method for prototyping and fabricating complex microwave circuits | 6,645,790 | 11/11/2003 |
| Linearity radio frequency switch with low control voltage | 6,642,578 | 11/4/2003 |
| Amplifier bias adjustment circuit to maintain high-output third-order intermodulation distortion performance | 6,639,466 | 10/28/2003 |
| Active clamping circuit for power amplifiers | 6,580,321 | 6/17/2003 |
| Active power splitter with impedance matching | 6,577,198 | 6/10/2003 |
| Low bias current/temperature compensation current mirror for linear power amplifier | 6,559,722 | 5/6/2003 |
| Wafer demount receptable for separation of thinned wafer from mounting carrier | 6,554,949 | 4/29/2003 |
| Bias circuit for use with low-voltage power supply | 6,515,546 | 2/4/2003 |
| Multi-band amplifier | 6,501,331 | 12/31/2002 |
| Wafer demount receptacle for separation of thinned wafer from mounting carrier | 6,491,083 | 12/10/2002 |
| Wafer demount gas distribution tool | 6,470,946 | 10/29/2002 |
| GaAs MESFET having LDD and non-uniform P-well doping profiles | 6,458,640 | 10/1/2002 |
| Electrical contactor for automatic testing of chips including RF chips | 6,437,585 | 8/20/2002 |

| Spatula for separation of thinned wafer from mounting carrier | 6,415,843 | 7/9/2002 |
|--|-----------|------------|
| Amplifier bias adjustment circuit to maintain high-output third-order intermodulation distortion performance | 6,404,284 | 6/11/2002 |
| Adjustable low spurious signal DC-DC converter | 6,314,008 | 11/6/2001 |
| Multiple-band amplifier | 6,242,986 | 6/5/2001 |
| Amplifier using a single polarity power supply | 6,005,375 | 12/21/1999 |
| Amplifier using a single polarity power supply | 5,952,860 | 9/14/1999 |
| Amplifier using a single polarity power supply and including depletion mode FET and negative voltage generator | 5,892,400 | 4/6/1999 |
| Multiple-band amplifier | 5,774,017 | 6/30/1998 |
| Multi-frequency local oscillators | 5,748,049 | 5/5/1998 |
| Method and apparatus for providing grounding to microwave circuit by low impedance means | 5,736,913 | 4/7/1998 |
| Automatic gain-control transimpedence amplifier | 5,646,573 | 7/8/1997 |

| U.S. PENDING PATENT APPLICATIONS | | ···· |
|---|------------|------------|
| TITLE | APP. NO. | APP, DATE |
| VCSEL ARRAY | 14/495,643 | 9/24/2014 |
| WIDE-BAND AMPLIFIERS USING CLIPPER CIRCUITS FOR REDUCED HARMONICS | 14/276,400 | 5/13/2014 |
| DOHERTY POWER AMPLIFIER WITH INTEGRATED PRE- DISTORTION | 14/292,241 | 5/30/2014 |
| DYNAMICALLY CONFIGURABLE BIAS CIRCUIT FOR CONTROLLING GAIN EXPANSION OF MULTI-MODE SINGLE CHAIN LINEAR POWER AMPLIFIERS | 14/456,975 | 8/11/2014 |
| CIRCUIT ARRANGEMENT FOR COMPENSATING CURRENT VARIATIONS IN CURRENT MIRROR CIRCUIT | 13/789,908 | 3/8/2013 |
| PROTECTION CIRCUIT | 13/910,802 | 6/5/2013 |
| SWITCHED INDUCTOR DC-DC CONVERTER | 13/286,660 | 11/1/2011 |
| SELF ESD PROTECTED DEVICE AND METHOD THEREOF | 13/459,621 | 4/30/2012 |
| INTEGRATED OUTPUT COMBINER FOR AMPLIFIER SYSTEM | 13/548,774 | 7/13/2012 |
| BOOST-BUCK DC-DC CONVERTER | 13/624,339 | 9/21/2012 |
| COMPACT DOHERTY COMBINER | 13/713,409 | 12/13/2012 |
| DOHERTY AMPLIFIER | 13/710,765 | 12/11/2012 |
| RADIO FREQUENCY (RF) COUPLERS | 14/026,461 | 9/13/2013 |
| REDUCTION OF DELAMINATION AND/OR DEVICE LIFT IN SEMICONDUCTOR PACKAGING | 61/918,750 | 12/20/2013 |
| PROGRAMMABLE BROAD BANDWIDTH GAIN AMPLIFIER | 61/895,868 | 10/25/2013 |

EXHIBIT C

Trademarks

| TITLE | REG. NO. | ISSUE DATE |
|---------------------------------|-----------------|------------|
| Anadigics logo – Korea | 40-0621551-0000 | 6/16/05 |
| Anadigics logo – United Kingdom | UK00002259306 | 6/29/01 |
| Anadigics logo – Israel | 146,149 | 9/3/02 |
| Anadigics logo – Japan | 4,773,176 | 5/21/04 |
| Anadigics logo – Taiwan | 01110808 | 7/16/04 |
| Anadigics logo – U.S. | 2,896,625 | 10/26/04 |

EXHIBIT D

Registered Mask Works

| Copyright | Registration | Exploitation | Full Title / Description |
|------------------|--------------|---|--|
| Number | Date | <u>Date</u> | |
| MW0000018366 | 2007-10-05 | 18Sep06 | C1051A_A (C9AGCS2B_E) single chip digital tuner / 4 |
| > (YYY0000010011 | | | semiconductor chips in housings + 2 col. composite plots |
| MW0000018716 | 2009-06-26 | 6Feb09 | H6551A_A (99K00700_E) Wilan power amplifier / 4 |
| | | | semiconductor chips in housings + 2 col. composite plots |
| MW0000018777 | 2009-08-03 | 5May09 | H6605A_A (H6224A_I) WCDMA/HSPA power |
| | | | amplifier / 4 semiconductor chips in housings + 2 col. |
| | | N. M. | composite plots |
| MW0000018962 | 2009-12-10 | 1Dec09 | H9966A_A (FE9266AB_A) Wlan dual bandTX/RX |
| | | | FEIC / 4 semiconductor chips in housings + 2 col. |
| | | | composite plots |
| MW0000018824 | 2009-10-20 | 13Aug09 | H9970B_E (FA280_Q) dual band WiMax power |
| | | | amplifier, 2.3-2.7 GHz & 3.3-3.8 GHz / 4 semiconductor |
| | | | chips + col. composite plot |
| MW0000018731 | 2009-05-12 | 26Nov07 | M1023B_A (USPT11D_E) GaAs upconverter for 1GHz |
| | | | integrated tuner product A1T1032 / 4 semiconductor |
| | | | chips in housings + 2 col. composite plots |
| MW0000018797 | 2009-06-26 | 13Jul07 | M2017A_E (BPGA5BDH_C) GaAs amplifier for |
| | | | DOCSIS 3.0 programmable gain amplifier/ 4 |
| | | | semiconductor chips in housings + 2 col. composite plots |
| MW0000018966 | 2009-12-14 | 14Mar08 | M3623A_B (3619DB_A) 1GHz three-way active power |
| | | | splitter optimized for MoCA enabled subscriber |
| | | | equipment / 4 semiconductor chips in housings + 2 col. |
| | | | composite plots |
| MW0000018730 | 2009-05-12 | 26Nov07 | C1032A_A (C18TIGER9A_A) CMOS down-conver for |
| | | | 1GHz integrated tuner product A1T1032 / 4 |
| | | 1 | semiconductor chips in housings + 2 col. composite plots |
| MW0000019044 | 2009-12-14 | 11Jan08 | C6155A_A (PC6155A_A) quad-band GSM/SPRS/edge |
| | | | power amplifier module with integrated power control / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019042 | 2009-12-14 | 15Nov09 | C6157A_G (PC6159A_D) CMOS controller / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000018963 | 2009-12-14 | 22Dec07 | H0155A_C (IX75C_A) quad-band GSM/SPRS/EDGE |
| | | | power module with integrated power control / 4 |
| | | | semiconductor chips in housings + 2 col. composite plots |
| MW0000018842 | 2009-10-30 | 1Jul09 | H6159A_A (1Z44B_A) LB die for AWE6169 polar |
| | | | PAM / 4 semiconductor chips + col. composite plot |
| MW0000018827 | 2009-09-16 | 7Nov07 | H6224A_D (H6224A_B) help3 dual-band 900 MHz/IMT |
| | | | UMTS 3.4V HSPA linear power amplifier module / 4 |
| | | | semiconductor chips + col. composite plot |
| MW0000018829 | 2009-09-16 | 7Nov07 | H6243B_D (H6243B_D) help3 1.7 GHz/UMTS |
| • | | | 3.4V/28.5 dBm linear power amplifier module / 4 |
| | | | semiconductor chips + col. composite plot |
| | | | |

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| MW0000018828 | 2009-09-16 | 28Sep07 | H6261A_B (WIMAX6261A_B) 2.5-2.7 GHz mobile |
|----------------------|------------|----------|--|
| AVI VV 0000018828 | 2009-09-10 | 263ср07 | WiMAX power amplifier module / 4 semiconductor |
| | | | chips + col. composite plot |
| MW0000018806 | 2009-11-18 | 10Nov09 | H6264B_B (K6264J_B) AWT6264 / 4 semiconductor |
| 14144 0000010000 | 2007-11-10 | 10110109 | chips + 2 col. composite plots |
| MW0000018830 | 2009-09-16 | 11Oct07 | H6309A_E (KPH01F_C) help2 AWS/KPCS CDMA |
| WW0000018850 | 2009-09-10 | 1100107 | 3.4V/28 dBm linear power amplifier module / 4 |
| | | | semiconductor chips + col. composite plot |
| MW0000018967 | 2009-12-14 | 28Aug08 | H6388A_C (C4507A_B) 450 MHz CDMA |
| 141 44 0000018307 | 2009-12-14 | ZoAugoo | 3.4V/29.5dBm linear power amplifier module / 4 |
| | | | |
| MW0000018798 | 2009-06-26 | 6Jul07 | semiconductor chips in housings + 2 col. composite plots |
| 101 00 00000 10 / 96 | 2009-00-20 | OJUIO7 | H6423A_A (Y3V25B_D) WiMAX power amplifier / 4 |
| MW0000019081 | 2010-08-02 | 18Dec09 | semiconductor chips in housings + 2 col. composite plots |
| 141.00000013091 | 2010-08-02 | 18Decu9 | H9935B_E (KPXEG10_E) AWL9935 Kilmer Peak FEM |
| MW0000018964 | 2010-01-20 | 12) (| B / 4 semiconductor chips + 2 col. composite plots |
| M W 0000018964 | 2010-01-20 | 13May08 | M2420A_B (CSD100NGC_B) high output power |
| | 77 | | doubler line amplifier / 4 semiconductor chips in |
| 3.63370000010065 | 2010 01 00 | 150.00 | housings + 2 col. composite plots |
| MW0000018965 | 2010-01-20 | 15Oct09 | M2447A_A (2UESD2407_B) 2UM line amp / 4 |
| 3 57730000010015 | | ļ | semiconductor chips in housings + 2 col. composite plots |
| MW0000019043 | 2010-01-20 | 22Aug08 | M3606A_C (AS1P5SKC_E) active power splitter / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019133 | 2010-09-29 | 12Apr10 | M3625A_A (APS3625_A) / 4 semiconductor chips + 2 |
| | | | col. composite plots |
| MW0000019130 | 2010-09-13 | 28Jul10 | C6157A_L (PC6157A_L) CMOS controller /4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019161 | 2010-09-13 | 25Jun10 | H0157A_B (HB6157C_D) high band linear pam /4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019078 | 2010-08-02 | 15Jan10 | H6283B_B (WMAX35D7_F) 3.5 GHz WiMax PA / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000018940 | 2010-04-12 | 1Apr10 | H6323A_B (C6323A_C) H0323A_B (P6323A_C) Help |
| | | | cell/PCS PA w/coupler /4 semiconductor chips in |
| | | | housings + 2 col. composite plots |
| MW0000019013 | 2010-04-08 | 29Aug09 | H6433A_A (Y3V35G_B) 3.4-3.6 GHz mobile WiMax /4 |
| | | | semiconductor chips in housings + 2 col. composite plots |
| MW0000019148 | 2010-10-06 | 30Oct10 | H6625A_A (B5402A_E) help4 cell /4 semiconductor |
| | | | chips + 2 col. composite plots |
| MW0000019149 | 2010-11-15 | 15Dec10 | H6628A_C (B8402C_G) help4 EGSM. /4 semiconductor |
| | | | chips + 2 col. composite plots |
| MW0000018939 | 2010-04-22 | 20Apr10 | H6701A_B (T27D_C) IMT/PCS HELP4PAM /4 |
| | 1 | | semiconductor chips in housings + 2 col. composite plots |
| MW0000019079 | 2010-08-25 | 23Aug10 | H6713A_B (B13H405C_B) band 13 help 4 PA / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019134 | 2010-10-16 | 25Sep10 | H9270A_C (927007_B) intel 2Ghz PA module / 4 |
| | | | semiconductor chips + 2 col. composite plots |
| MW0000019041 | 2010-01-13 | 11Dec09 | H9555A_A (PA5344BB_B) WiFi FEIC / 4 |
| | | 125005 | semiconductor chips + 2 col. composite plots |
| MW0000018951 | 2010-03-23 | 18Dec09 | H9935B_C (KPXEG3_B) front end integrated circuit / 4 |
| 1,17, 0000010731 | 2010-03-23 | 1000009 | semiconductor chips in housings + 2 col. composite plots |
| | <u></u> | | semiconductor emps in nousings + 2 cor. composite plots |

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| MW0000019343 | 2012-08-14 | 19Jul12 | H0526A_B (G5HB06D_B) highband die for GOBI 5k module / 4 semiconductor chips in housings + col. composite plots |
|--------------|------------|---------|---|
| MW0000019353 | 2012-09-24 | 26Jul12 | H6181A_B (Alt6181P1_H) Alt6181 MMPA / 4 semiconductor chips in housing + col. composite plots |
| MW0000019350 | 2012-10-23 | 10ct12 | H6340B_B (OJT05_H) HELP CDMA band class 0,10 high efficiency power amplifier module / 5 semiconductor chips in housings + col. composite plots. |
| MW0000019342 | 2012-08-14 | 18Jul12 | H6526A_B (G5LB40A_B) lowband die for GOBI 5k module / 4 semiconductor chips in housings + col. composite plots |
| MW0000019346 | 2012-04-26 | 3Apr12 | H6615A_E (15CA_G)/H0615A_E (15P2A_I) HELP3E Cell/PCS PA / 4 semiconductor chips in housings + col. composite plots |
| MW0000019344 | 2012-04-26 | 3Apr12 | H6618A_D (18E2A_D)/H0618A_D (18I3A_D) HELP3E EGSM/IMTPA / 4 semiconductor chips in housings + col. composite plots |
| MW0000019347 | 2012-05-09 | 788 | M2445A_A (2444NP029J_A) 870 Mhz hyrid line amp / 4 semiconductor chips in housings + col. composite plots |
| MW0000019351 | 2012-09-24 | 26Jul12 | MMPA06A_A laminate type 15R / 4 semiconductor chips + col. composite plots |
| MW0000019355 | 2012-09-24 | 26Jul12 | WH0181A_D (HX04F_I) MMPA / 5 semiconductor chips in housing + col. composite plots |
| MW0000019354 | 2012-09-24 | 26Jul12 | WH6181A_C (L06WE_B) Alt6181 MMPA / 5 semiconductor chips in housing + col. composite plots |
| MW0000019442 | 2013-02-19 | 4Oct12 | H7223A_B (K7223_DS_MIR_B) dual die amp / 4 semiconductor chips in housings + col. plots |
| MW0000019434 | 2013-02-19 | 4Oct12 | H7223A_B (K7223DS_B) dual die amp / 4 semiconductor chips in housings + col. plots |
| MW0000019446 | 2013-02-19 | 31Oct12 | H7227A_B (K7227_DS_MIR_B) dual die amp 4 semiconductor chips in housings + col. plots / |
| MW0000019441 | 2013-02-19 | 31Oct12 | H7227A_B (K7227DS_B) dual die amp / 4 semiconductor chips in housings + col. plots |
| MW0000019438 | 2013-02-19 | 5Apr12 | H7228A_A (K7228A4_A) dual die amp / 4 semiconductor chips in housings + col. plots |
| MW0000019440 | 2013-02-19 | 5Apr12 | H7228A_A (K7228A4_MIR_A) dual die amp / 4 semiconductor chips in housings + col. plots |
| MW0000019452 | 2013-05-29 | 02Feb13 | H7230A_A (JWMX35D7_MIR_H) / 4 semiconductor chips in housings + col. compsite plots |
| MW0000019451 | 2013-05-29 | 06Mar13 | H9280B_A (FE2563DD_B) / 4 semiconductor chips + col. composite plots |
| MW0000019450 | 2013-05-29 | 10Mar13 | H9281A_A (FE2582CB_A) / 4 semiconductor chips + col. composite plots |
| MW0000019453 | 2013-05-29 | 10Mar13 | H9580B_A (WLANFEIC_A) / 4 semiconductor chips in housings + col. compsite plots |
| MW0000019439 | 2013-03-22 | 6Mar13 | H9581B_D (FE5792DE1LL_A) 5GHz WLAN front end module. / 4 semiconductor chips in housings + col. plots. |

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RECORDED: 10/27/2014